256K x 1 Bit Static RAM

FEATURES

- **Fast Access Time 25, 35, 45ns (max.)**
- **Low Power Dissipation**
  Standby (TTL): 2mA (max.)
  (CMOS): 100μA (max.)
  Operating : 100mA (max.)
- **Single 5V ± 10% supply**
- **TTL compatible inputs and output**
- **Full Static Operation**
  —No clock or refresh required
- **Tristate Output**
- **Low Data Retention Current: 50μA (max.)**
- **Battery Back-up Operation**
  —2V (min.) Data Retention
- **Standard 24-pin DIP (300 mil)**

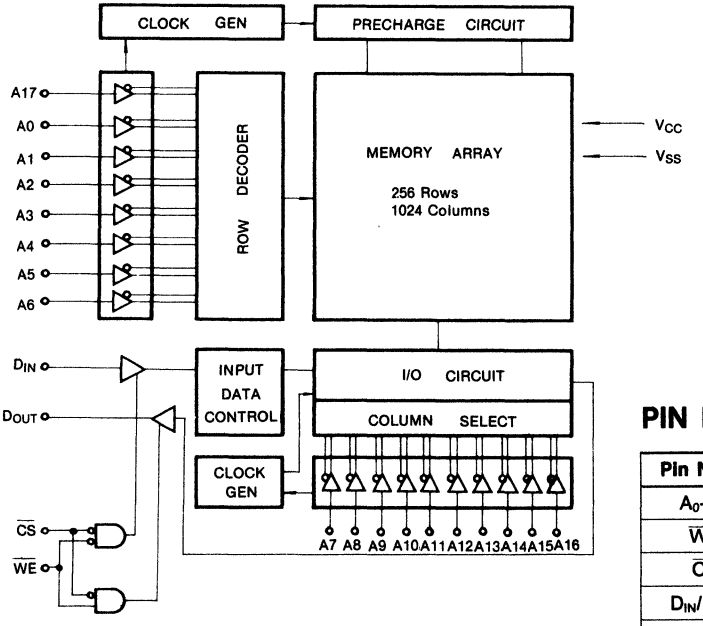
GENERAL DESCRIPTION

The KM61257 is a 262,144-bit high speed Static Random Access Memory organized as 262,144 words by 1 bit. The device is fabricated using Samsung's advanced CMOS process.

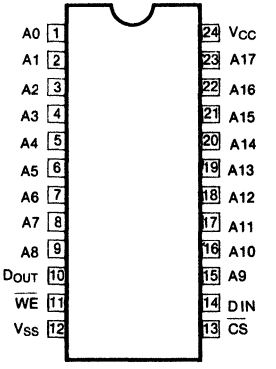
The KM61257 has a chip enable input for the minimum current power down mode.

The KM61257 has been designed for high speed applications. It is particularly well suited for the use in high speed and low power applications in which battery back up for nonvolatility is required.

FUNCTION BLOCK DIAGRAM



PIN CONFIGURATION



PIN NAMES

Pin Name	Pin Function
A_0-A_{17}	Address Inputs
$\overline{WE}$	Write Enable
$\overline{CS}$	Chip Select
D_{IN}/D_{OUT}	Data Inputs/Outputs
V_{CC}	+5V Power Supply
V_{SS}	Ground